

Features

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.2V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.001 grams (approximate)

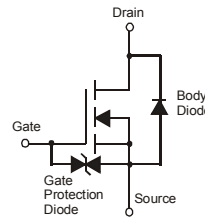
DFN1006H4-3



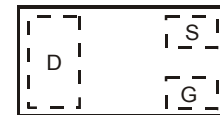
ESD PROTECTED



BOTTOM VIEW



Equivalent Circuit



TOP VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±10	V
Drain Current (Note 1)	I _D	300	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Total Power Dissipation (Note 1) @T _A = 25°C	P _D	350	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	357	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	@ T _C = 25°C V _{DS} = 30V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10 ±500	μA nA	V _{GS} = ±10V, V _{DS} = 0V V _{GS} = ±5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	0.6	—	1.2	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	2.2 1.5 1.2	Ω	V _{GS} = 1.8V, I _D = 20mA V _{GS} = 2.5V, I _D = 20mA V _{GS} = 4.0V, I _D = 100mA
Forward Transconductance	Y _{fs}	100	—	—	mS	V _{DS} = 10V, I _D = 0.1A
Source-Drain Diode Forward Voltage	V _{SD}	0.5	—	1.4	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	39	—	pF	V _{DS} = 3V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	10	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	3.6	—	pF	
Switching Time	Turn-on Time	t _{on}	—	11	nS	V _{DD} = 5V, I _D = 10 mA, V _{GS} = 0-5V
	Turn-off Time	t _{off}	—	51	nS	

- Notes:
1. Device mounted on FR-4 PCB, pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Short duration pulse test used to minimize self-heating effect.

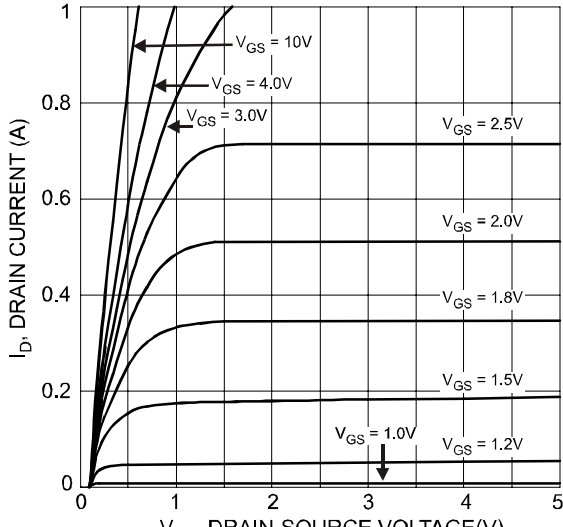


Fig. 1 Typical Output Characteristics

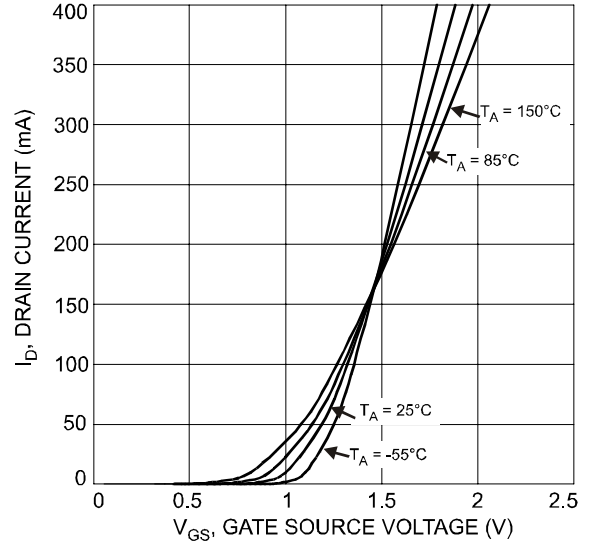


Fig. 2 Typical Transfer Characteristics

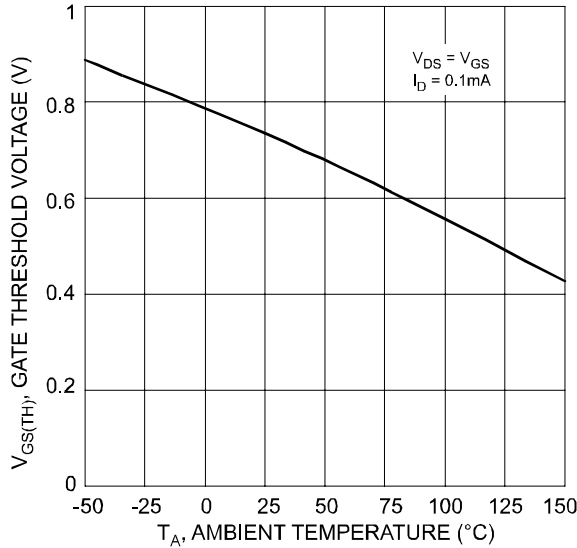


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

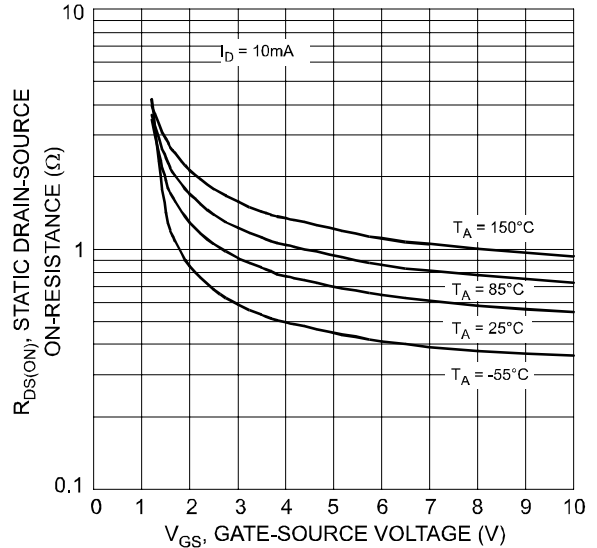


Fig. 4 Static Drain-Source On-Resistance vs. Gate-Source Voltage

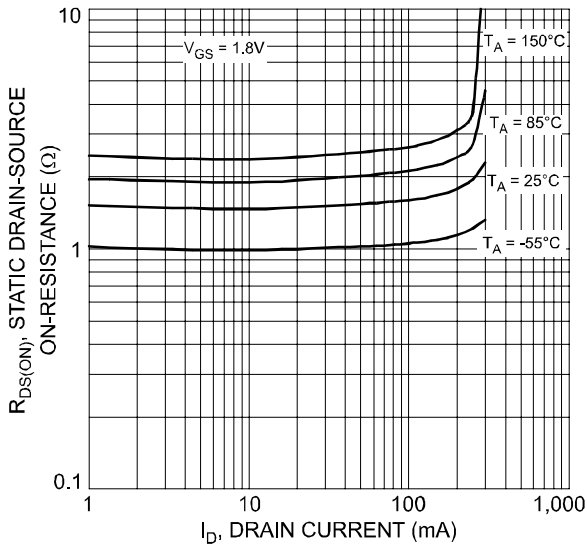


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

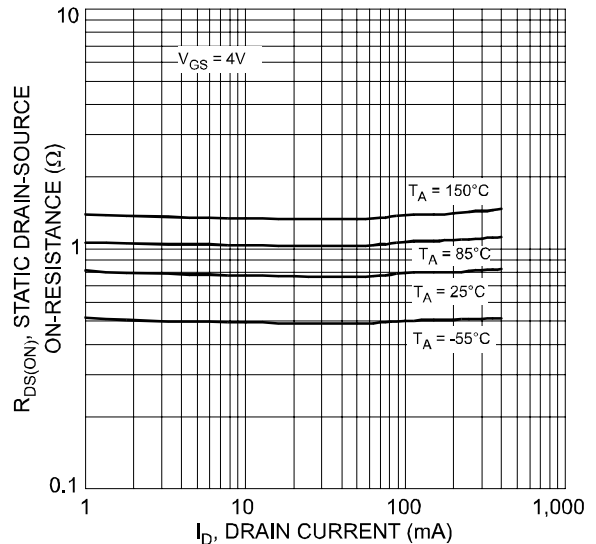


Fig. 6 Static Drain-Source On-Resistance vs. Drain Current

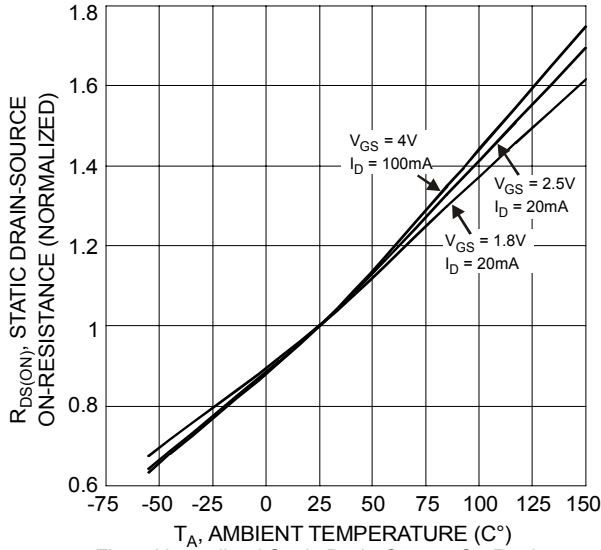


Fig. 7 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

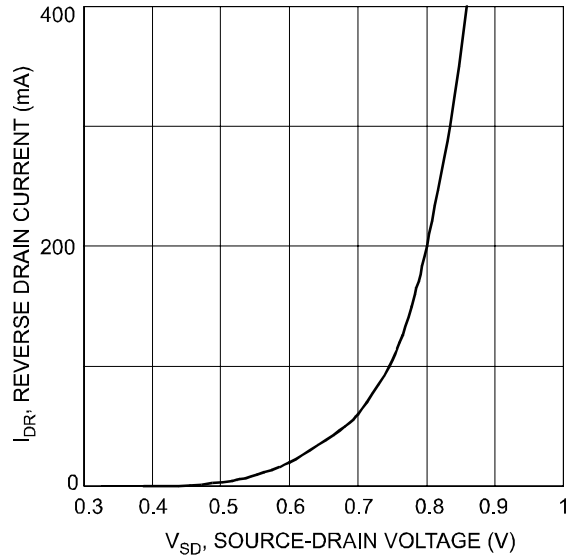


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

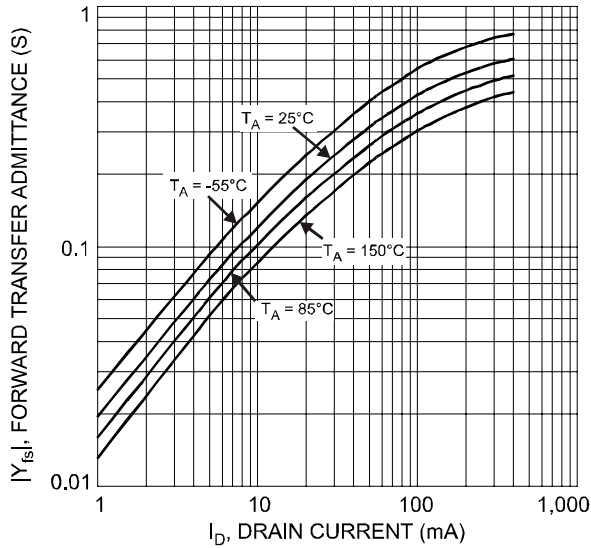


Fig. 9 Forward Transfer Admittance vs. Drain Current

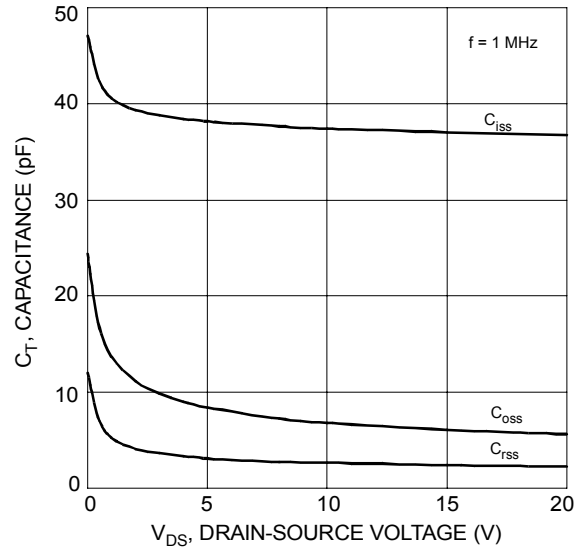


Fig. 10 Typical Capacitance

Ordering Information (Note 5)

Part Number	Case	Packaging
DMN32D2LFB4-7	DFN1006H4-3	3000/Tape & Reel

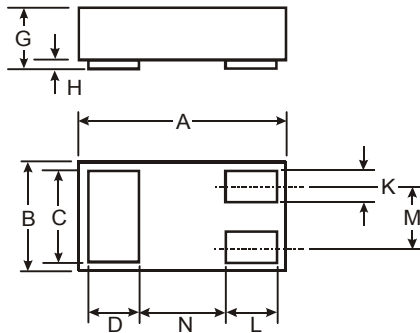
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



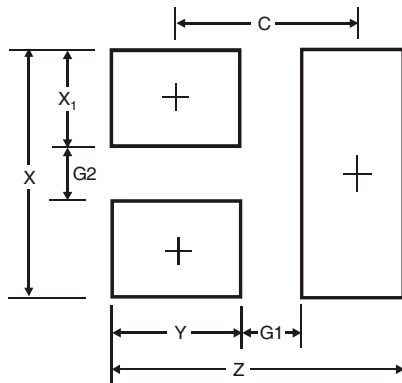
DV = Product Type Marking Code

Package Outline Dimensions



DFN1006-3			
Dim	Min	Max	Typ
A	0.95	1.075	1.00
B	0.55	0.675	0.60
C	0.45	0.55	0.50
D	0.20	0.30	0.25
G	0.47	0.53	0.50
H	0	0.05	0.03
K	0.10	0.20	0.15
L	0.20	0.30	0.25
M	—	—	0.35
N	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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